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Green Products

RMB2S-RMB6S Miniature Glass Passivated Fast Recovery Surface Mount Bridge Rectifiers

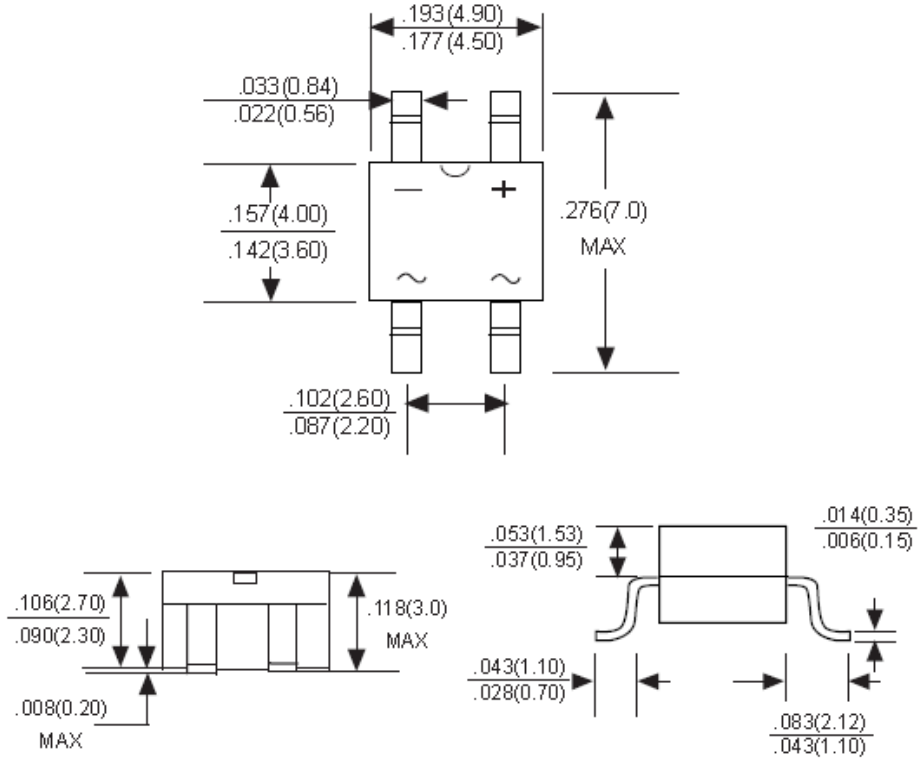
Features:

- **Ideal for printed circuit board**
- **Reliable low cost construction utilizing molded plastic technique**
- **High temperature soldering guaranteed:260°C/10 seconds at 5 lbs., (2.3kg) tension**
- **Small size, simple installation**
- **High surge current capability**
- **This is a Pb − Free Device**
- **All SMC parts are traceable to the wafer lot**
- **Additional testing can be offered upon request**

Mechanical Data:

- **Case: Molded plastic body**
- **Terminals: Plated leads solderable per MIL-STD-750, Method 2026**
- **Polarity: Polarity symbols marked on case**
- **Mounting Position: Any**
- **Weight: 0.0044 ounce, 0.126 grams**

Mechanical Dimensions: In Inches/mm



MB-S

RMB2S-RMB6S

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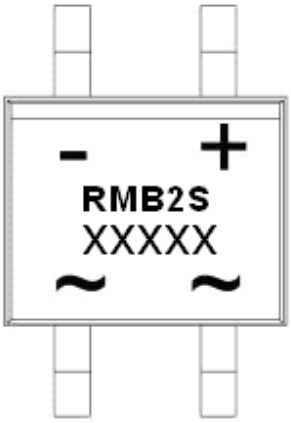
Marking Diagram:



Where XXXXX is YYWWL

RMB2S = Part Name
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
RMB2S-RMB6S	MB-S (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

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Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified

Single Phase half wave 60Hz, resistive or inductive load. For capacitive load current derate by 20%.

Characteristic	Symbol	RMB2S	RMB4S	RMB6S	Units
Maximum repetitive peak reverse voltage	V_{RRM}	200	400	600	V
RMS Reverse Voltage	$V_{R(RMS)}$	140	280	420	
Maximum DC blocking voltage	V_{DC}	200	400	600	
Maximum average forward current 60Hz sine save resistance load On glass-epoxy P.C.B. On aluminum substrate	$I_{F(AV)}$	0.5 0.8			A
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30			A
Maximum instantaneous forward voltage drop (Note 1)@ I_F = 0.4A	V_F	1.0			V
Maximum DC reverse current T_A = 25°C at rated DC blocking voltage T_A = 125°C	I_R	5 100			μA
Maximum reverse recovery time(Note 2)	trr	150			nS
Typical junction capacitance (per leg)	Cj	13			pF
Typical thermal resistance	$R_{\theta JA}$	85			°C/W
Operating junction and storage temperature range	T_J,T_{STG}	-55 to +150			°C

Note: 1. Pulse Test with PW=300us, 1% Duty Cycle
2. Reverse Recovery Test Condition: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A

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FIG. 1- DERATING CURVE OUTPUT RECTIFIED CURRENT FOR

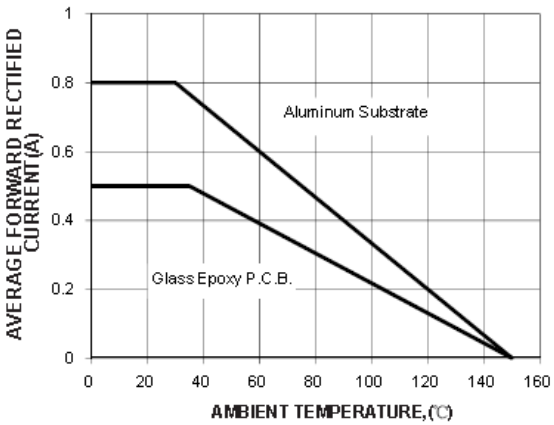


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT PERLEG

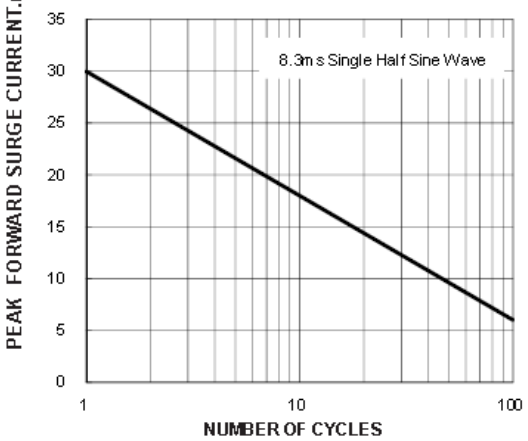


FIG. 3-TYPICAL FORWARD VOLTAGE CHARACTERISTICS PER LEG

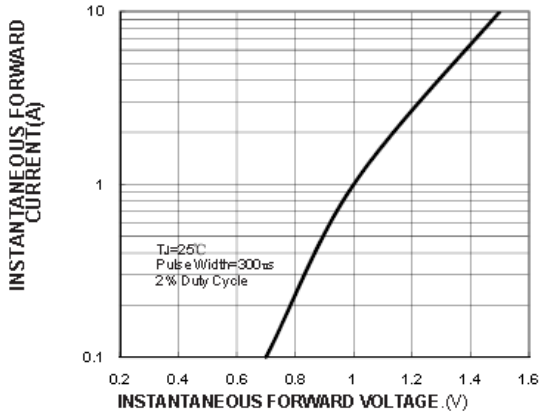


FIG. 4-TYPICAL REVERSE LEAKAGE CHARACTERISTICS PER LEG

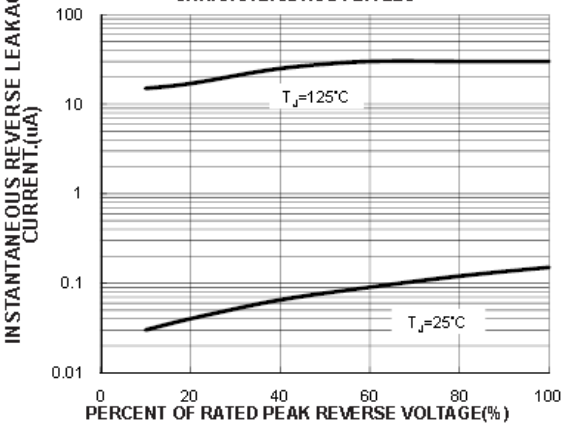
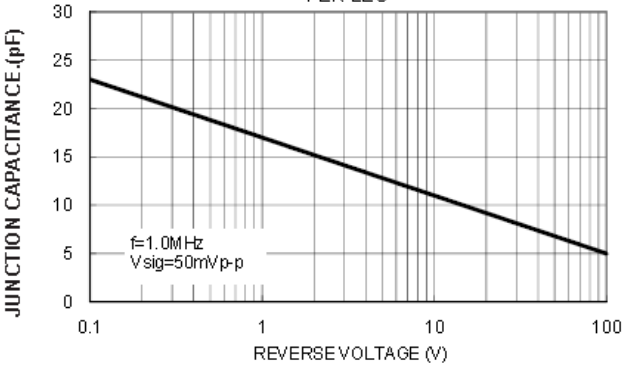


FIG. 5 TYPICAL JUNCTION CAPACITANCE PER LEG



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